

AMENDMENTS TO THE CLAIMS:

Please cancel claims 32-34 and 52-59 without prejudice or disclaimer, and add new claims 63-73, as follows:

1-40. (Canceled).

41. (Previously Added) A plasma processing method for removing a photoresist film covering a layer formed at a workpiece placed within a processing chamber, wherein the layer has an opening and a fence portion distending toward the upper portion of a surrounding edge of the opening, the processing method comprising:

applying high-frequency power for biasing to the workpiece at a first power level;

raising the processing gas to a plasma; and

switching the high-frequency power for biasing applied to the workpiece

from the first power level to a second power level lower than the first

power level before the photoresist film becomes completely removed.

42. (Previously Added) A plasma processing method according to claim 41, wherein the fence portion is removed during applying high-frequency power for biasing to the workpiece at the first power level.

43. (Previously Added) A plasma processing method according to claim 41, wherein the first power level is switched to the second power level due to removing the fence portion.

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

44. (Previously Added) A plasma processing method according to claim 41, wherein the layer is an SiO₂ film formed at the workpiece.
45. (Previously Added) A plasma processing method according to claim 41, wherein the layer is an organic film formed at the workpiece.
46. (Previously Added) A plasma processing method for removing a photoresist film covering a layer formed at a workpiece placed within a processing chamber, comprising:
- etching the layer;
 - applying high-frequency power for biasing to the workpiece at a first power level and removing a fence portion distending toward the upper portion of a surrounding edge of an opening formed at the layer during the etching step;
 - raising the processing gas to a plasma; and
 - switching the high-frequency power for biasing applied to the workpiece from the first power level to a second power level lower than the first power level before the photoresist film becomes completely removed.
47. (Previously Added) A plasma processing method according to claim 46, wherein the layer is an SiO₂ film formed at the workpiece.
48. (Previously Added) A plasma processing method according to claim 46, wherein the layer is an organic film formed at the workpiece.

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HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
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49. (Previously Added) A plasma processing method for removing a photoresist film formed at a workpiece placed within a processing chamber, comprising:
- applying high-frequency power for biasing to the workpiece;
 - raising the processing gas to a plasma;
 - ashing the photoresist film while applying the high-frequency power for biasing to the workpiece; and
 - after the ashing step, stopping application of the high-frequency power for biasing before the photoresist film becomes completely removed, while utilizing the same type of processing gas both before and after stopping application of the high-frequency power.
50. (Previously Added) A plasma processing method according to claim 49, wherein the photoresist film constitutes a mask used to form a specific pattern at an SiO₂ film formed at the workpiece.
51. (Previously Added) A plasma processing method according to claim 49, wherein the photoresist film constitutes a mask used to form a specific pattern at an organic film formed at the workpiece.
- 52-59. (Canceled).
60. (Previously Added) A plasma processing method for removing a photoresist film having an opening pattern with a larger opening area than an opening area of a hole formed at a specific layer of a workpiece, the opening of the hole contained in the opening pattern when the specific layer is etched to a middle portion thereof by utilizing the photoresist film as a mask, comprising:
- applying high-frequency power for biasing to the workpiece;

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

raising the processing gas to a plasma;

ashing the photoresist while applying the high-frequency power for biasing
to the workpiece; and

after the ashing step, stopping the application of the high-frequency power
for biasing before the photoresist film becomes completely removed.

61. (Previously Added) A plasma processing method according to claim 60, wherein the specific layer is an SiO₂ film formed at the workpiece.
62. (Previously Added) A plasma processing method according to claim 60, wherein the specific layer is an organic film formed at the workpiece.
63. (New) A plasma processing method comprising:
etching a film by utilizing a resist film as a mask;
thereafter removing the resist film substantially halfway with biasing
power; and
thereafter removing the remaining resist film completely without applying
any biasing power.
64. (New) A plasma processing method according to claim 63, wherein the resist film constitutes a mask used to form a specific pattern at an SiO₂ film formed at the workpiece.
65. (New) A plasma processing method according to claim 63, wherein the resist film constitutes a mask used to form a specific pattern at an organic film formed at the workpiece.
66. (New) A plasma processing method for removing a photoresist film covering a layer formed at a workpiece, wherein the layer has an opening, the photoresist

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

film has an opening pattern exposing the opening of the layer, the opening pattern of the photoresist film is larger than the opening of the layer, and the opening of the layer has a fence portion of the layer distending upwardly, the processing method comprising:

raising a processing gas to a plasma;

applying a biasing power to the workpiece;

removing the photoresist film substantially halfway with the fence portion;

thereafter, stopping application of the biasing power with the photoresist

film remaining; and

thereafter, removing the photoresist film completely, while utilizing the

processing gas same as the processing gas for removing the

photoresist film substantially halfway.

67. (New) A plasma processing method according to claim 66, wherein the fence portion is removed during applying biasing power to the workpiece at the first power level.
68. (New) A plasma processing method according to claim 66, wherein the first power level is switched to the second power level due to removing the fence portion.
69. (New) A plasma processing method according to claim 66, wherein the layer is an SiO₂ film formed at the workpiece.
70. (New) A plasma processing method according to claim 66, wherein the layer is an organic film formed at the workpiece.

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com

71. (New) A plasma processing method for removing a photoresist film covering a layer formed at a workpiece, wherein the layer has an opening, and the photoresist film has an opening pattern exposing the opening of the layer, the opening pattern of the photoresist film is larger than the opening of the layer, the processing method comprising:
- etching the layer;
 - raising a processing gas to a plasma;
 - removing a fence portion of the layer formed during the etching process and distending toward the upper portion of the opening while applying biasing power to the workpiece; and
 - thereafter, stopping application of the biasing power with the photoresist film remaining.
72. (New) A plasma processing method according to claim 71, wherein the layer is an SiO₂ film formed at the workpiece.
- 73 (New) A plasma processing method according to claim 71, wherein the layer is an organic film formed at the workpiece.